



## DECLARATION

As a below-named inventor, I hereby declare that:

My residence, post office address, and citizenship are as stated below next to my name.

I believe I am an original, first and joint inventor of the subject matter that is claimed and for which a patent is sought on the invention entitled:

### **"ACTIVE ELECTRONIC DEVICES BASED ON GALLIUM NITRIDE AND ITS ALLOYS GROWN ON SILICON SUBSTRATES WITH BUFFER LAYERS OF SiCAIN"**

the specification of which is serial no. 10/663,168 filed on September 15, 2003.

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment specifically referred to herein.

I acknowledge the duty to disclose information that is material to patentability as defined in Title 37, Code of Federal Regulations, § 1.56.

I hereby claim foreign priority benefits under Title 35, United States Code § 119(a)-(d) or (f) or § 365(b) of any foreign application(s) for patent or inventor's certificate, or § 365(a) of any PCT international application which designated at least one country other than the United States of America, listed below and have also identified below any foreign application for patent or inventor's certificate, or of any PCT international application having a filing date before that of the application on which priority is claimed.

Prior Foreign Application Number(s)	Country	Foreign Filing Date	Priority Claimed (Yes/No)	Certified Copy Attached? (Yes/No)
PCT/US02/33134	PCT	October 16, 2002	Yes	No

I hereby claim the benefit under Title 35, United States Code § 119(e) of any United States provisional application(s) listed below.

Application Number(s)	Filing Date
60/410,859	September 13, 2002

I hereby claim the benefit under Title 35, United States Code § 120 of any United States application(s), or § 365(c) of any PCT international application designating the United States of America, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT International application in the manner provided by the first paragraph of Title 35, United States Code § 112, I acknowledge the duty to disclose

Declaration

New U.S. Application Based on 09/981,024

Title: ACTIVE ELECTRONIC DEVICES BASED ON GALLIUM NITRIDE AND ITS ALLOYS GROWN ON SILICON SUBSTRATES WITH BUFFER LAYERS OF SiCAIN

information which is material to patentability as defined in Title 37, Code of Federal Regulations § 1.56 which became available between the filing date of the prior application and the national or PCT international filing date of this application.

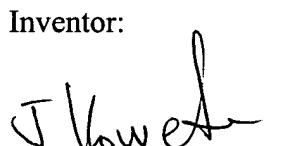
U.S. Parent Application Number	PCT Parent Number	Parent Filing Date	Parent Patent Number (if applicable)
09/965,022		September 26, 2001	
09/981,024		October 16, 2001	09/965,022

I request that all correspondence be directed to:

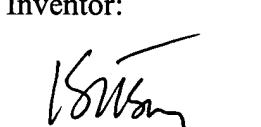
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I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

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Declaration

New U.S. Application Based on 09/981,024

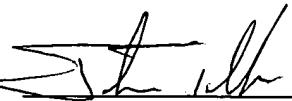
Title: ACTIVE ELECTRONIC DEVICES BASED ON GALLIUM NITRIDE AND ITS ALLOYS GROWN ON  
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